

EX
G1
13. (*Twice Amended*) A semiconductor integrated circuit device according to any one of claims 4 or 5, wherein said second electrostatic protection element is a MOS field effect transistor, the drain of which is connected to said power source wire, and the source and the gate of which are connected to said ground potential wire.

Please add the following new claims:

EX
G1
30. (*New*) The semiconductor integrated circuit device according to claim 1, wherein said electrostatic protection element is a bipolar transistor that comprises a substrate having a first conductive type and two diffusion layers having a second conductive type which is opposite to the first conductive type, said two diffusion layers disposed so as to closely face each other.

31. (*New*) The semiconductor integrated circuit device according to claim 1, wherein said electrostatic protection element is a thyristor that comprises a substrate having a first conductive type and two diffusion layers respectively having a first conductive type and a second conductive type which is opposite to the first conductive type, arranged so as to closely face each other, and by further forming on a well having the second conductive type provided on said substrate having the first conductive type two diffusion layers respectively having the first conductive type and the second conductive type, so as to closely face each other.

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32. (New) The semiconductor integrated circuit device according to claim 1, wherein said electrostatic protection element is a diode that comprises a substrate or a well having a first conductive type and two diffusion layers having a second conductive type which is opposite to the first conductive type, said two diffusion layers disposed so as to closely face each other.
